

LISTINT OF THE CLAIMS

1-44. (Cancelled).

45. (Currently Amended) A semiconductor device comprising:

an insulating layer;

an ~~ammonia-cleaned, etched~~ opening in said insulating layer, said opening having sidewalls and a bottom, said bottom being substantially free of polymer residue and silicon rich oxide residue; and

a conductor in said ~~ammonia-cleaned, etched~~ opening.

46. (Currently Amended) An integrated circuit comprising:

an ammonia-cleaned, ~~etch residue-free~~ High Aspect Ratio opening provided in an insulating layer, said opening being formed over a polysilicon region and a bottom of said opening being substantially free of polymer residue and silicon rich oxide residue; and

a conductor within said opening, said conductor being electrically connected with said polysilicon region.

47. (Previously Presented) An integrated circuit as in claim 46 further comprising a silicide layer between said conductor and said polysilicon region.

48. (Original) An integrated circuit as in claim 46, wherein said integrated circuit is a memory circuit.

49. (Original) An integrated circuit as in claim 47 wherein the interface area between said conductor and polysilicon region is free of oxygen contamination.

50-53. (Cancelled).